

[Document Name] ABSTRACT

[Abstract]

[Problem] The object is to provide a semiconductor production apparatus including an improved susceptor as a wafer support and an improved susceptor supporting shaft, which can yield an epitaxially grown silicon film having a substantially uniform thickness.

[Means of Solution] An epitaxial growth apparatus 10A is of a single wafer processing type, which processes semiconductor wafers or silicon wafers W one by one, and comprises a process chamber 12 of silica glass and a susceptor 14A disposed within the process chamber 12 for supporting a silicon wafer W as semiconductor wafer. The susceptor 14A is supported and positioned by the shaft 15A at only the peripheral portion in the lower surface thereof. A side portion of the process chamber 12 is formed with an inlet 16 for a process gas. Also, a side portion of the process chamber 12 is formed with an outlet 18 at a position opposite from the inlet 16. A plurality of halogen lamps 20 are radially disposed with an appropriate arrangement in each of areas above and below the process chamber 12.

[Selected Drawing] Fig. 1